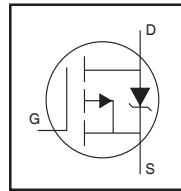


# AUIRF9Z34N

HEXFET® Power MOSFET

## Features

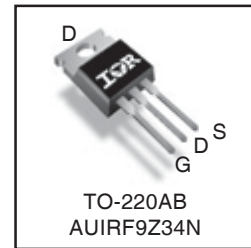
- Advanced Planar Technology
- P-Channel MOSFET
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified\*



|                   |              |
|-------------------|--------------|
| $V_{(BR)DSS}$     | <b>-55V</b>  |
| $R_{DS(on)}$ max. | <b>0.10Ω</b> |
| $I_D$             | <b>-19A</b>  |

## Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



|          |          |          |
|----------|----------|----------|
| <b>G</b> | <b>D</b> | <b>S</b> |
| Gate     | Drain    | Source   |

## Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature ( $T_A$ ) is 25°C, unless otherwise specified.

|                                 | Parameter  | Max.               | Units |
|---------------------------------|--|--------------------|-------|
| $I_D @ T_C = 25^\circ\text{C}$  | Continuous Drain Current, $V_{GS} @ 10\text{V}$          | -19                | A     |
| $I_D @ T_C = 100^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$          | -14                |       |
| $I_{DM}$                        | Pulsed Drain Current ①                                   | -68                |       |
| $P_D @ T_C = 25^\circ\text{C}$  | Power Dissipation  | 68                 | W     |
|                                 | Linear Derating Factor                                   | 0.45               | W/°C  |
| $V_{GS}$                        | Gate-to-Source Voltage                                   | ± 20               | V     |
| $E_{AS}$                        | Single Pulse Avalanche Energy (Thermally Limited)②       | 180                | mJ    |
| $I_{AR}$                        | Avalanche Current ①                                      | -10                | A     |
| $E_{AR}$                        | Repetitive Avalanche Energy ①                            | 6.8                | mJ    |
| dv/dt                           | Peak Diode Recovery dv/dt ③                              | -5.0               | V/ns  |
| $T_J$                           | Operating Junction and                                   | -55 to + 175       | °C    |
| $T_{STG}$                       | Storage Temperature Range                                |                    |       |
|                                 | Soldering Temperature, for 10 seconds (1.6mm from case ) |                    |       |
|                                 | Mounting Torque, 6-32 or M3 screw                        | 10 lbf•in (1.1N•m) |       |

## Thermal Resistance

|                 | Parameter                           | Typ. | Max. | Units |
|-----------------|-------------------------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ⑤                  | —    | 2.2  | °C/W  |
| $R_{\theta CS}$ | Case-to-Sink, Flat, Greased Surface | 0.50 | —    |       |
| $R_{\theta JA}$ | Junction-to-Ambient                 | —    | 62   |       |

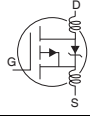
HEXFET® is a registered trademark of International Rectifier.

\*Qualification standards can be found at <http://www.irf.com/>

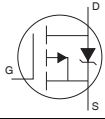
### Static Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

|                                 | Parameter                            | Min. | Typ. | Max. | Units    | Conditions  |
|---------------------------------|--------------------------------------|------|------|------|----------|---|
| $V_{(BR)DSS}$                   | Drain-to-Source Breakdown Voltage    | -55  | —    | —    | V        | $V_{GS} = 0V, I_D = -250\mu A$                        |
| $\Delta V_{(BR)DSS}/\Delta T_J$ | Breakdown Voltage Temp. Coefficient  | —    | 0.05 | —    | V/°C     | Reference to $25^\circ\text{C}, I_D = -1\text{mA}$    |
| $R_{DS(on)}$                    | Static Drain-to-Source On-Resistance | —    | —    | 0.10 | $\Omega$ | $V_{GS} = -10V, I_D = -10A$ ④                         |
| $V_{GS(th)}$                    | Gate Threshold Voltage               | -2.0 | —    | -4.0 | V        | $V_{DS} = V_{GS}, I_D = -250\mu A$                    |
| $g_{fs}$                        | Forward Transconductance             | 4.2  | —    | —    | S        | $V_{DS} = -25V, I_D = -10A$                           |
| $I_{DSS}$                       | Drain-to-Source Leakage Current      | —    | —    | -25  | $\mu A$  | $V_{DS} = -55V, V_{GS} = 0V$                          |
|                                 |                                      | —    | —    | -250 |          | $V_{DS} = -44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$ |
| $I_{GSS}$                       | Gate-to-Source Forward Leakage       | —    | —    | 100  | nA       | $V_{GS} = 20V$  |
|                                 | Gate-to-Source Reverse Leakage       | —    | —    | -100 |          | $V_{GS} = -20V$                                       |

### Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

|              | Parameter                       | Min. | Typ. | Max. | Units | Conditions   |
|--------------|---------------------------------|------|------|------|-------|--|
| $Q_g$        | Total Gate Charge               | —    | —    | 35   | nC    | $I_D = -10A$<br>$V_{DS} = -44V$<br>$V_{GS} = -10V$ , See Fig. 6 & 13 ④   |
| $Q_{gs}$     | Gate-to-Source Charge           | —    | —    | 79   |       |  |
| $Q_{gd}$     | Gate-to-Drain ("Miller") Charge | —    | —    | 16   |       |  |
| $t_{d(on)}$  | Turn-On Delay Time              | —    | 13   | —    | ns    | $V_{DD} = -28V$<br>$I_D = -10A$<br>$R_G = 13\Omega$<br>$R_D = 2.6\Omega$ , See Fig. 10 ④   |
| $t_r$        | Rise Time                       | —    | 55   | —    |       |  |
| $t_{d(off)}$ | Turn-Off Delay Time             | —    | 30   | —    |       |  |
| $t_f$        | Fall Time                       | —    | 41   | —    |       |  |
| $L_D$        | Internal Drain Inductance       | —    | 4.5  | —    | nH    | Between lead,<br>6mm (0.25in.)<br>from package<br>and center of die contact  |
| $L_S$        | Internal Source Inductance      | —    | 7.5  | —    |       |  |
| $C_{iss}$    | Input Capacitance               | —    | 620  | —    | pF    | $V_{GS} = 0V$<br>$V_{DS} = -25V$<br>$f = 1.0\text{MHz}$ , See Fig. 5   |
| $C_{oss}$    | Output Capacitance              | —    | 280  | —    |       |  |
| $C_{rss}$    | Reverse Transfer Capacitance    | —    | 140  | —    |       |  |

### Diode Characteristics

|          | Parameter                                 | Min.  | Typ. | Max. | Units | Conditions  |
|----------|---|---|------|------|-------|---|
| $I_S$    | Continuous Source Current<br>(Body Diode) | —   | —    | -19  | A     | MOSFET symbol<br>showing the<br>integral reverse<br>p-n junction diode.  |
| $I_{SM}$ | Pulsed Source Current<br>(Body Diode) ①   | —   | —    | -68  |       |   |
| $V_{SD}$ | Diode Forward Voltage                     | —   | —    | -1.6 | V     | $T_J = 25^\circ\text{C}, I_S = -10A, V_{GS} = 0V$ ④   |
| $t_{rr}$ | Reverse Recovery Time                     | —   | 54   | 82   | ns    | $T_J = 25^\circ\text{C}, I_F = -10A$  |
| $Q_{rr}$ | Reverse Recovery Charge                   | —   | 110  | 160  | nC    | $di/dt = 100A/\mu s$ ④  |
| $t_{on}$ | Forward Turn-On Time                      | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ ) |      |      |       |   |

#### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 3.6\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = -10A$ . (See Figure 12)
- ③  $I_{SD} \leq -10A$ ,  $di/dt \leq -290A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ\text{C}$ .
- ④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .
- ⑤  $R_{\theta}$  is measured at  $T_J$  approximately  $90^\circ\text{C}$ .

## Qualification Information†

|                                   |                      |   |     |
|-----------------------------------|----------------------|---|-----|
| <b>Qualification Level</b>        |                      | Automotive<br>(per AEC-Q101) ††   |     |
|                                   |                      | Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. |     |
| <b>Moisture Sensitivity Level</b> |                      | TO-220  | N/A |
| <b>ESD</b>                        | Machine Model        | Class M3 (+/- 250V)†††<br>AEC-Q101-002  |     |
|                                   | Human Body Model     | Class H1B (+/- 800V)†††<br>AEC-Q101-001   |     |
|                                   | Charged Device Model | Class C5 (+/- 2000V)†††<br>AEC-Q101-005   |     |
| <b>RoHS Compliant</b>             |                      | Yes   |     |

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

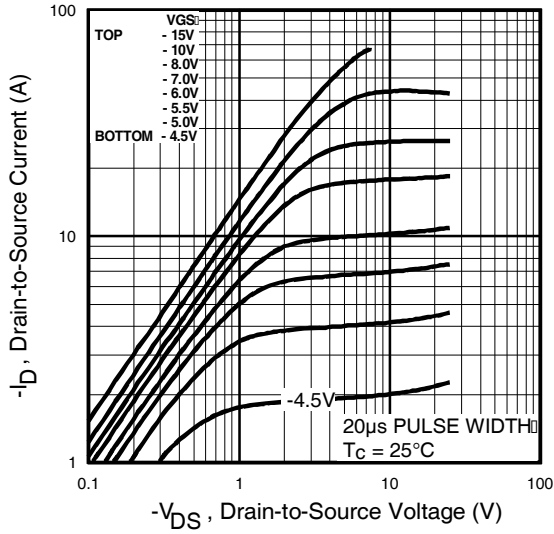


Fig 1. Typical Output Characteristics

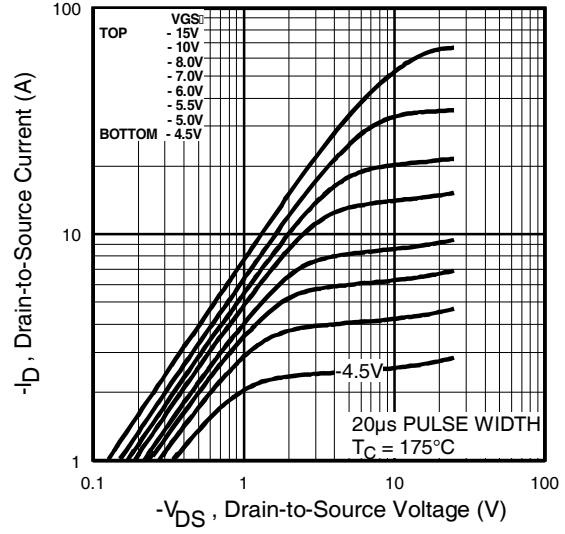


Fig 2. Typical Output Characteristics

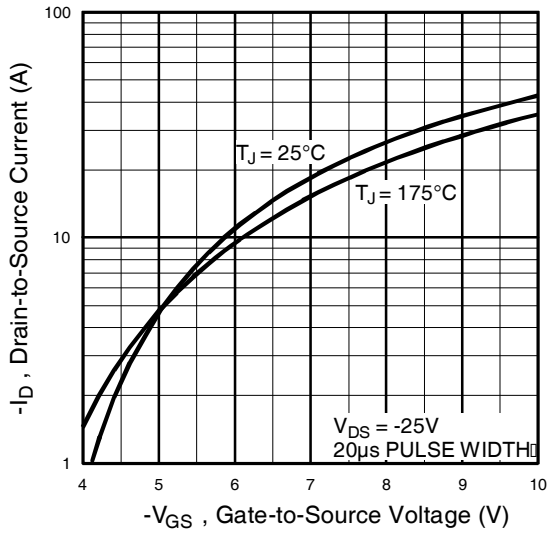


Fig 3. Typical Transfer Characteristics

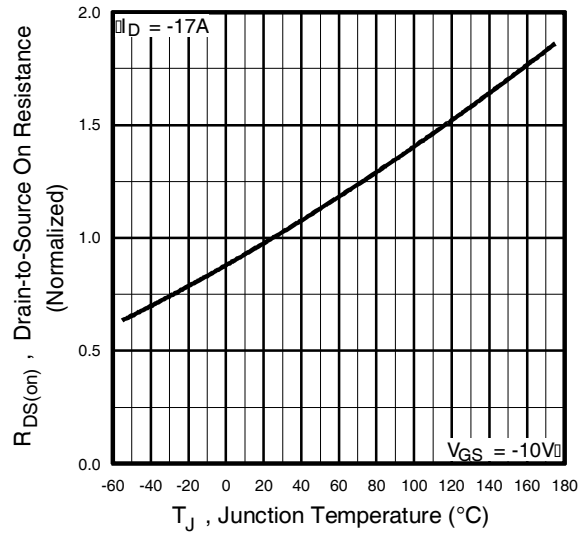
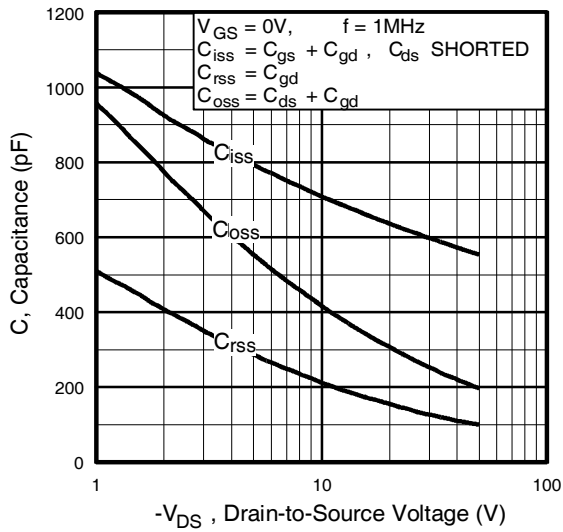
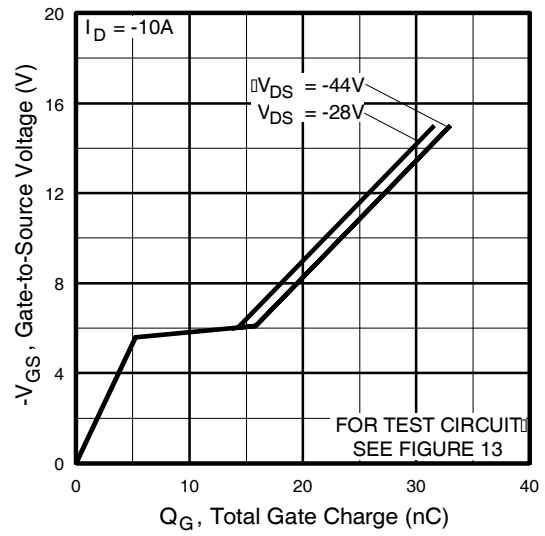


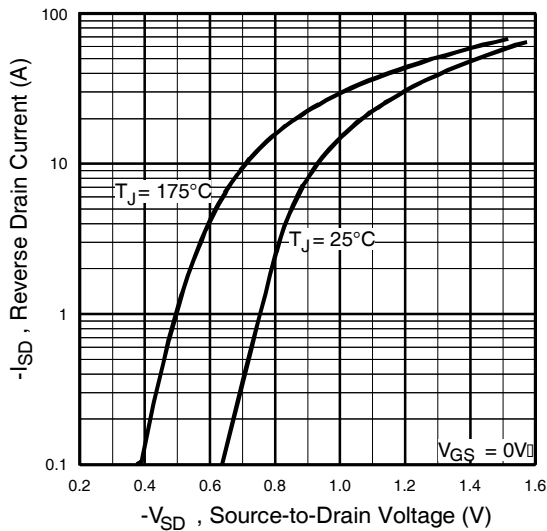
Fig 4. Normalized On-Resistance Vs. Temperature



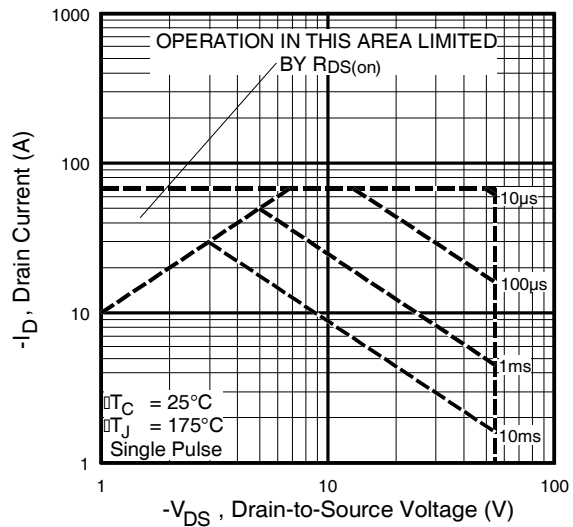
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



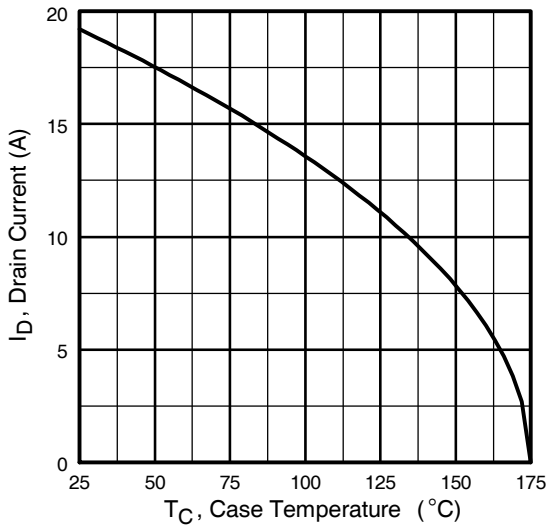
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



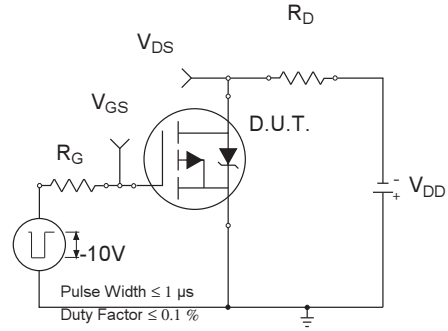
**Fig 7.** Typical Source-Drain Diode Forward Voltage



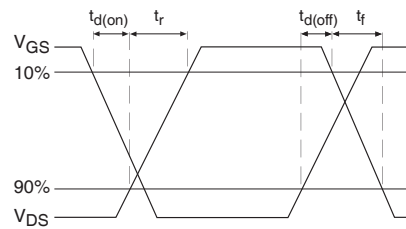
**Fig 8.** Maximum Safe Operating Area



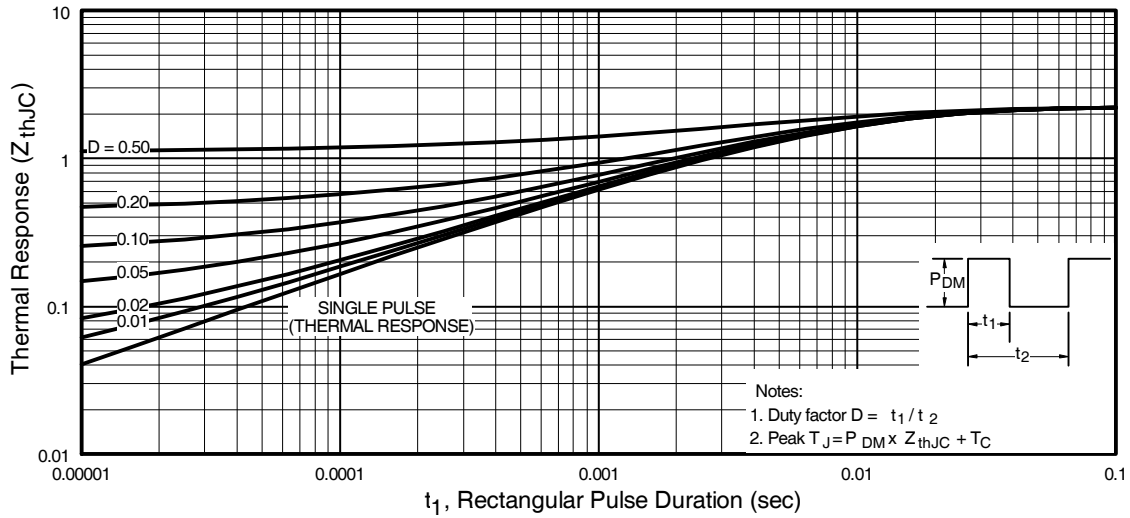
**Fig 9.** Maximum Drain Current Vs. Case Temperature



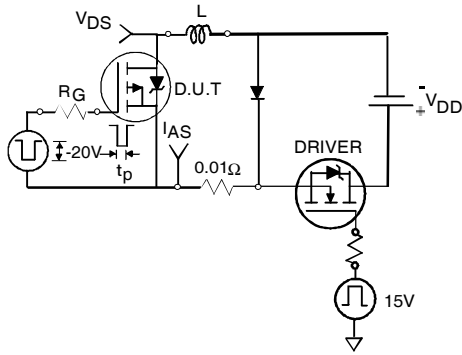
**Fig 10a.** Switching Time Test Circuit



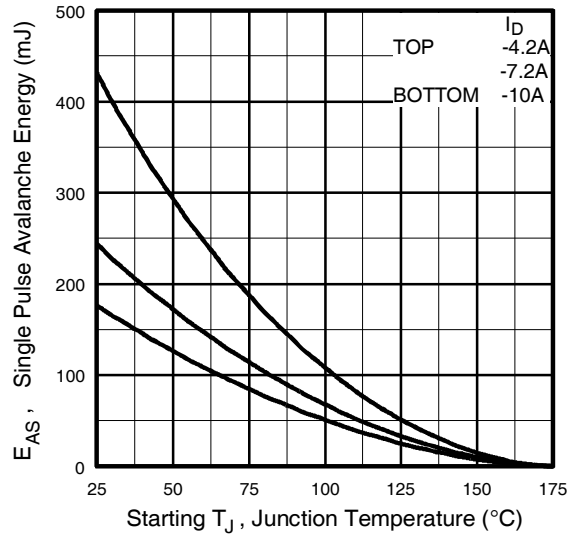
**Fig 10b.** Switching Time Waveforms



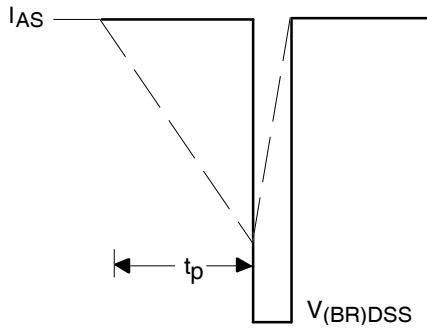
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



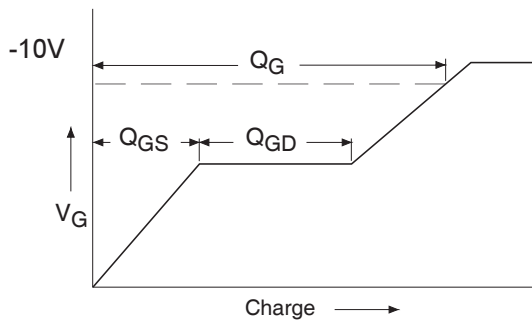
**Fig 12a.** Unclamped Inductive Test Circuit



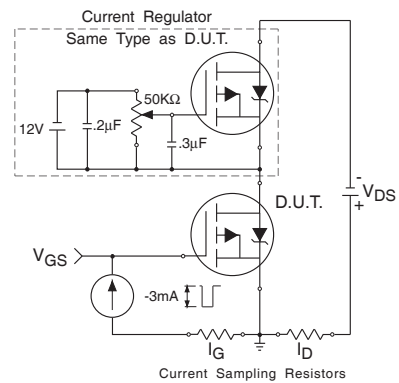
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 12b.** Unclamped Inductive Waveforms

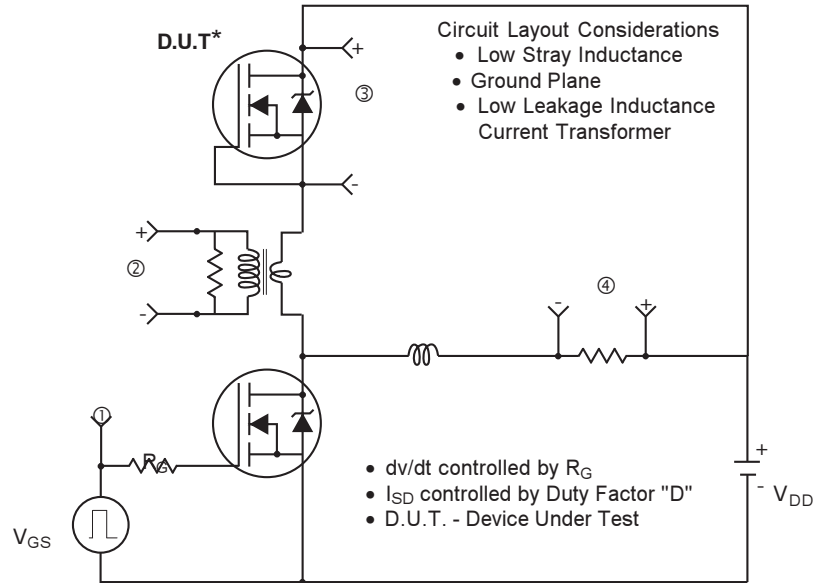


**Fig 13a.** Basic Gate Charge Waveform

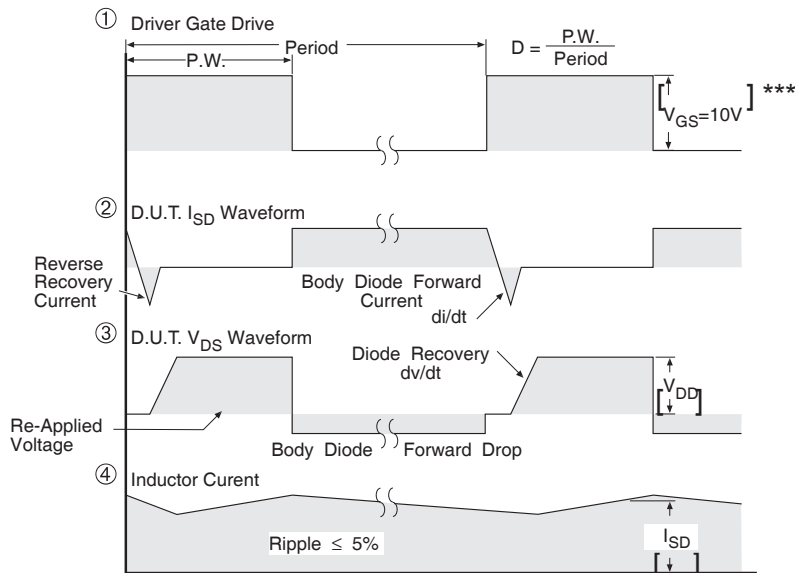


**Fig 13b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity of D.U.T for P-Channel



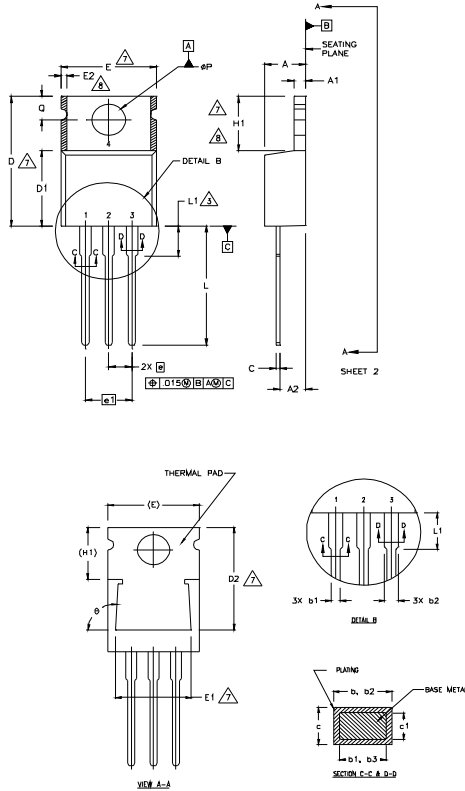
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 14.** For P-Channel HEXFETS



## TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



**NOTES:**

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3 LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5 DIMENSION b1 & c1 APPLY TO BASE METAL ONLY.
- 6 CONTROLLING DIMENSION - INCHES.
- 7 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

**LEAD ASSIGNMENTS**

**HERFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs CoPACK**

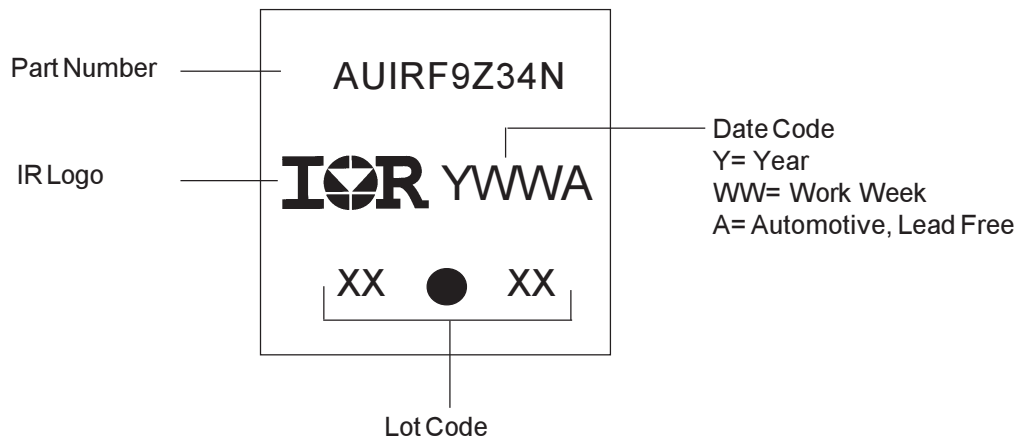
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

**DIODES**

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

| SYMBOL | DIMENSIONS  |       |         |      | NOTES |
|--------|-------------|-------|---------|------|-------|
|        | MILLIMETERS |       | INCHES  |      |       |
|        | MIN.        | MAX.  | MIN.    | MAX. |       |
| A      | 3.56        | 4.82  | .140    | .190 |       |
| A1     | 0.51        | 1.40  | .020    | .055 |       |
| A2     | 2.04        | 2.92  | .080    | .115 |       |
| b      | 0.38        | 1.01  | .015    | .040 |       |
| b1     | 0.38        | 0.96  | .015    | .038 | 5     |
| b2     | 1.15        | 1.77  | .045    | .070 |       |
| b3     | 1.15        | 1.73  | .045    | .068 |       |
| c      | 0.36        | 0.61  | .014    | .024 |       |
| c1     | 0.36        | 0.56  | .014    | .022 | 5     |
| D      | 14.22       | 16.51 | .560    | .650 | 4     |
| D1     | 8.38        | 9.02  | .330    | .355 |       |
| D2     | 12.19       | 12.88 | .480    | .507 | 7     |
| E      | 9.66        | 10.66 | .380    | .420 | 4,7   |
| E1     | 8.38        | 8.89  | .330    | .350 | 7     |
| e      | 2.54        | BSC   | .100    | BSC  |       |
| e1     | 5.08        |       | .200    | BSC  |       |
| H1     | 5.85        | 6.55  | .230    | .270 | 7,8   |
| L      | 12.70       | 14.73 | .500    | .580 |       |
| L1     | -           | 6.35  | -       | .250 | 3     |
| øP     | 3.54        | 4.08  | .139    | .161 |       |
| Q      | 2.54        | 3.42  | .100    | .135 |       |
| ø      | 90°-93°     |       | 90°-93° |      |       |

## TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

# AUIRF9Z34N

International  
**IOR** Rectifier

## Ordering Information

| Base part number | Package Type | Standard Pack |          | Complete Part Number |
|------------------|--------------|---------------|----------|----------------------|
|                  |              | Form          | Quantity |                      |
| AUIRF9Z34N       | TO-220       | Tube          | 50       | AUIRF9Z34N           |

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Tel: (310) 252-7105